CIR-V4SESR2408G

DDR4 SO-DIMM 2400MHz 8GB with ECC

Description

This specification defines the electrical and mechanical requirements for 260 pin, 1.2 V (VDD), Double Data Rate, Synchronous DRAM Dual In-Line Memory Modules (DDR4 SDRAM ECC SO-DIMM). This DDR4 ECC SO-DIMMs is intended for use as main memory when installed in PCs, laptops and other systems.

Reference design examples are included which provide an initial basis for DDR4 ECC SO-DIMM designs. Modifications to these reference designs may be required to meet all system timing, signal integrity and thermal requirements for DDR4-2400 support.

All DDR4 ECC SO-DIMM implementations must use simulations and lab verification to ensure proper timing requirement and signal integrity in the design.

Specifications

Density	8GB
Pin Count	260pin
Type	Unbuffered
Dimensions	69.6mm x 30.0mm
ECC	with ECC
Component Config	1G x 8 bit
Data Rate	2400 MHz
CAS Latency	17
Voltage	1.2V
PCB Layers	8
Operating Temp.(TCASE)	0°C~+85°C
Module Ranks	Single Rank

Features

- JEDEC Standard 260-pin Small-Outline Dual In-Line Memory Module
- VDD=VDDQ = 1.2V±0.06V   (1.14V~1.26V)
- Programmable CAS Latency(posted CAS): 11,12,13,14,15,16,17
- Inputs and Outputs are SSTL-12 compatible
- Low-Power auto self-refresh (LPASR)
- DRAMs have 16 internal banks for concurrent operation (4 Bank Group of 4banks each)
- Normal and Dynamic On-Die Termination for data, strobe and mask signals.
- Data bus inversion (DBI) for data bus
- Fixed burst chop (BC) of 4 and burst length (BL) of 8 via the MRS
- Selectable BC4 or BL8 on-the fly (OTF)
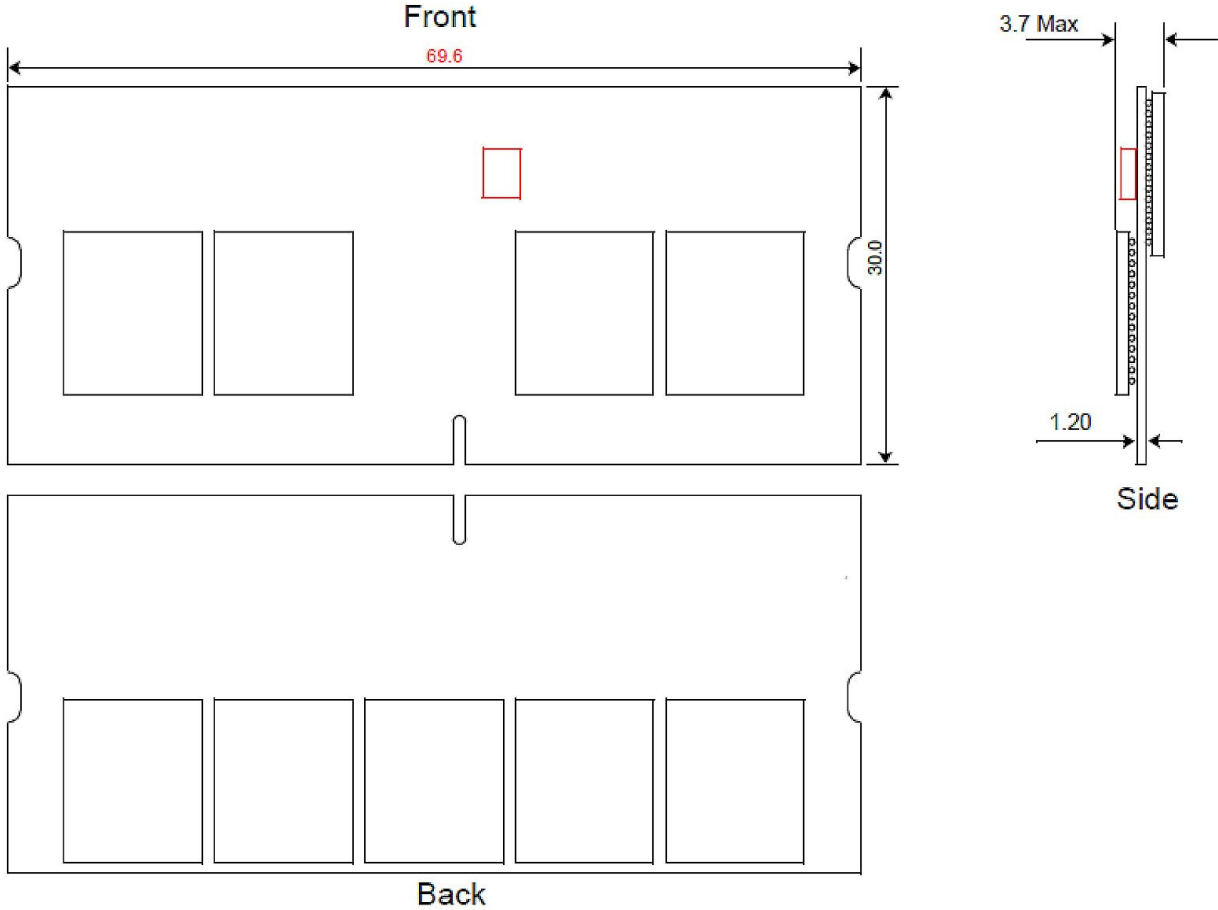- ECC function support
- RoHS and Halogen free

Speed Grade

Frequency Grade	Data Transfer Rate	CAS Latency Support							CL-tRCD-tRP
		CL11	CL12	CL13	CL14	CL15	CL16	CL17	
DDR4-2400	PC4-19200	1600	1600	1866	1866	2133	2133	2400	17-17-17

Package Dimensions

Unit: mm

Front

69.6

30.0

3.7 Max

1.20

Side

Back

Tolerances : ± 0.15mm unless otherwise specified